MJE200

Rev.E Mar.-2016

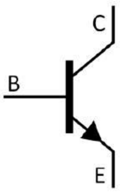
DATA SHEET

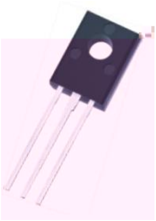
TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

\- MJE210

Low collector-emitter saturation voltage, high current gain bandwidth product, Complement to MJE210.

Designed for general audio amplifier applications.



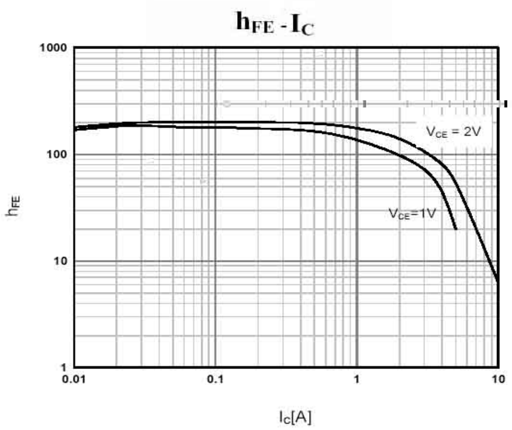


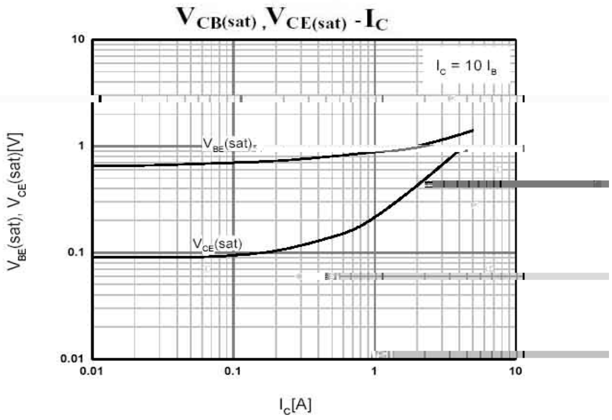
PIN1 Emitter PIN 2 Collector PIN 3 Base

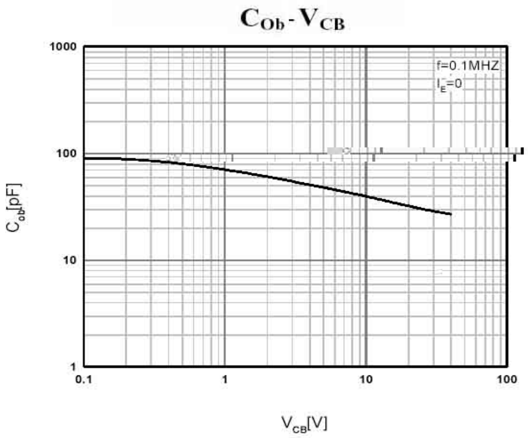
/ h_{FE} Classifications & Marking

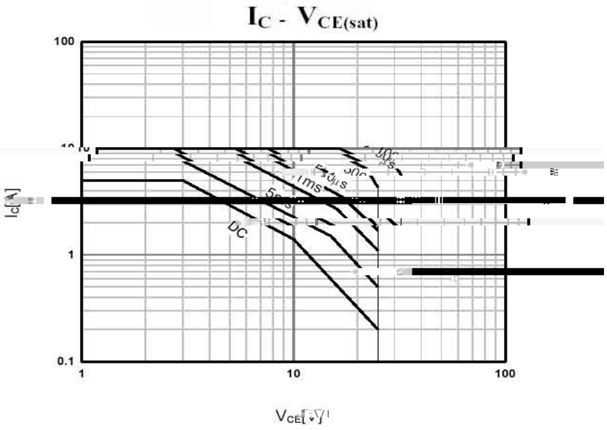
See Marking Instructions.

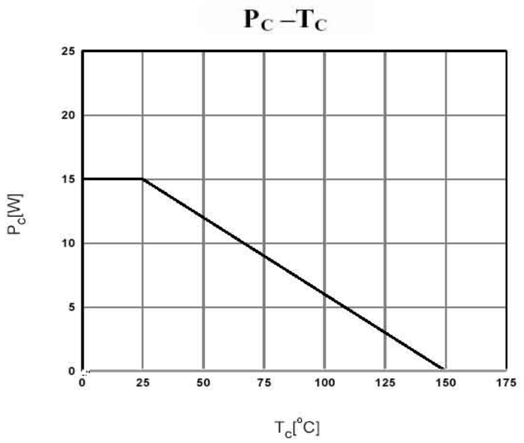
/ Electrical Characteristic Curve



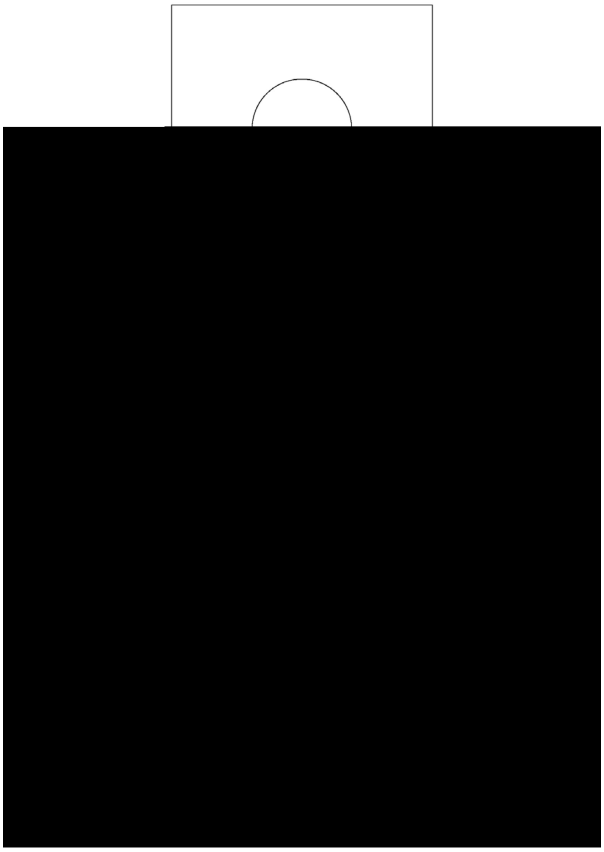








/ Marking Instructions



BR

MJE200

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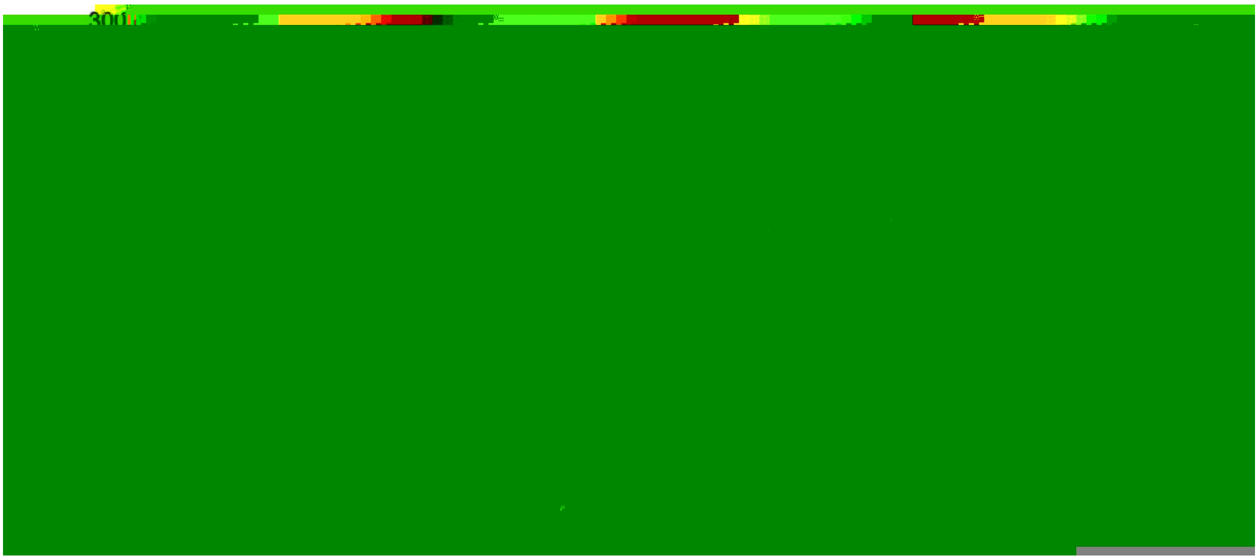
Note:

BR:	Company Code
MJE200:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1	25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm^3)

/ TUBE

Package Type	Units					Dimension		(unit mm^3)

/ Notices